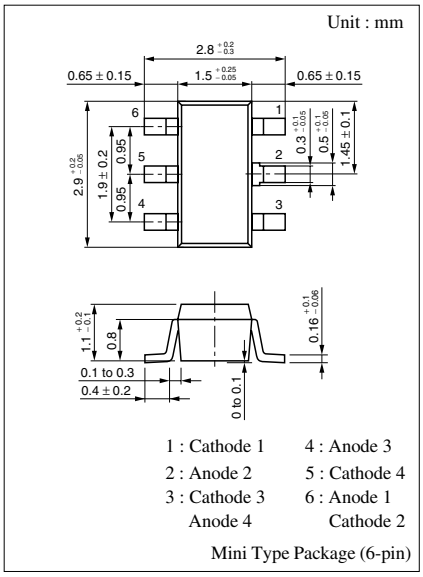
MA6X125

Silicon epitaxial planar type

For switching circuits



■ Features

- Four-element contained in one package, allowing high-density mounting

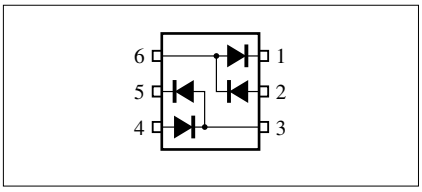
■ Absolute Maximum Ratings $T_a = 25°C$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	40	V
Peak reverse voltage	V_{RM}	40	V
Forward current (DC)*	I_F	100	mA
Peak forward current*	I_{FM}	200	mA
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	−55 to +150	°C

Note) *1 : Value for single diode

Marking Symbol: M2I

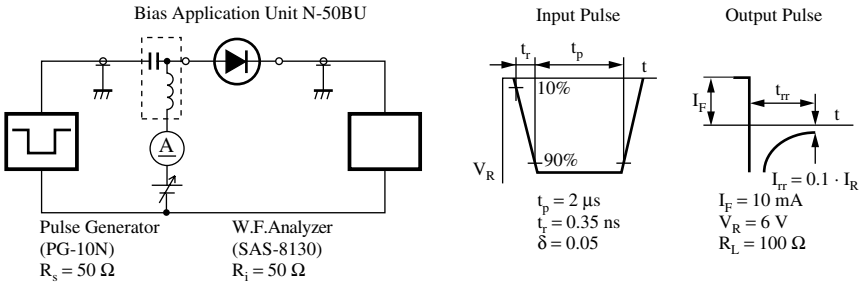
Internal Connection



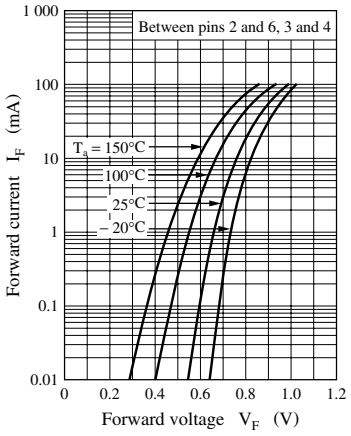
■ Electrical Characteristics $T_a = 25°C$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 40$ V			100	nA
Forward voltage (DC)	V_F	$I_F = 100$ mA			1.2	V
Reverse voltage (DC)	V_R	$I_R = 100$ µA	40			V
Terminal capacitance	C_t	$V_R = 0$ V, f = 1 MHz			5	pF
Reverse recovery time*3	t_{rr1} *1	$I_F = 10$ mA, $V_R = 6$ V		150		ns
	t_{rr2} *2	$I_{rr} = 0.1 \cdot I_R$, $R_L = 100\ \Omega$		90		

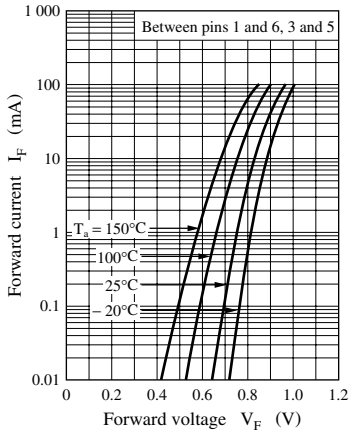
Note) 1. Rated input/output frequency: 100 MHz
2. *1 : Between pins 1 and 6, Between pins 3 and 5
*2 : Between pins 2 and 6, Between pins 3 and 4
*3 : t_{rr} measuring circuit



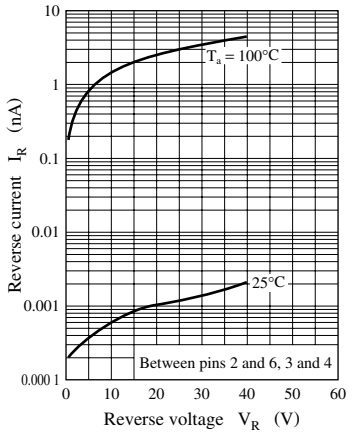
I_F — V_F



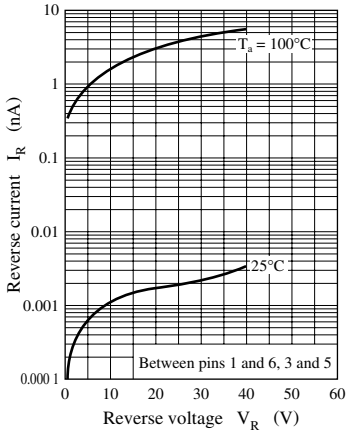
I_F — V_F



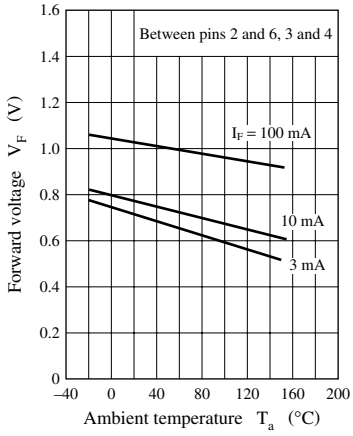
I_R — V_R



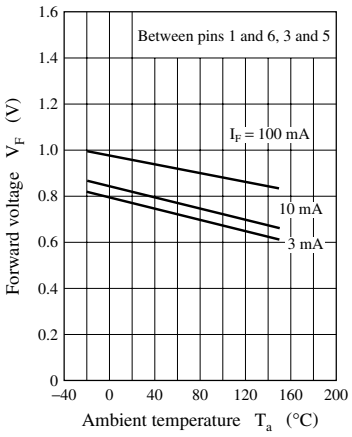
I_R — V_R



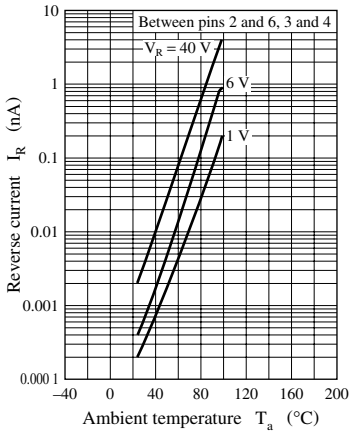
V_F — T_a



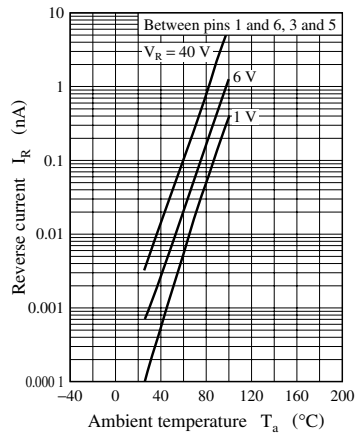
V_F — T_a



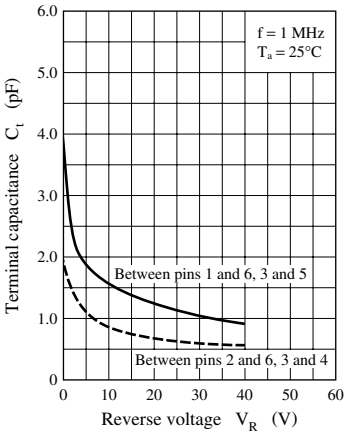
I_R— T_a

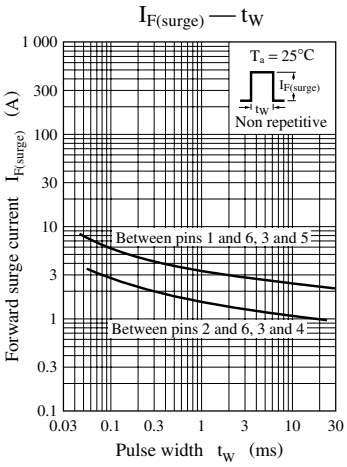


I_R — T_a



C_t — V_R




$I_{F(surge)}$ — t_W
T_a = 25°C
$I_{F(surge)}$
t_W
Non repetitive
Between pins 1 and 6, 3 and 5
Between pins 2 and 6, 3 and 4
Forward surge current $I_{F(surge)}$ (A)
1 000
300
100
30
10
3
1
0.3
0.1
0.03
0.1
0.3
1
3
10
30
Pulse width t_W (ms)